

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
17 November 2022 (17.11.2022)



(10) International Publication Number
WO 2022/240726 A1

(51) International Patent Classification:

H01L 21/3065 (2006.01) C23C 16/24 (2006.01)
H01L 21/3213 (2006.01) C23C 16/56 (2006.01)
C23C 16/02 (2006.01)

(21) International Application Number:

PCT/US2022/028285

(22) International Filing Date:

09 May 2022 (09.05.2022)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

17/319,885 13 May 2021 (13.05.2021) US
17/319,888 13 May 2021 (13.05.2021) US

(71) Applicant: **GLOBALWAFERS CO., LTD.** [CN/CN];
No. 8 Industrial East Road 2, Science-Based Industrial Park,
Hsinchu (TW).

(72) Inventor: **WANG, Gang**; 501 Pearl Drive, St. Peters, Mis-
souri 63376 (US).

(74) Agent: **SCHUTH, Richard A.** et al.; ARMSTRONG
TEASDALE LLP, 7700 Forsyth Blvd., Suite 1800, St.
Louis, Missouri 63105 (US).

(81) Designated States (*unless otherwise indicated, for every
kind of national protection available*): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,
CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO,
DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN,
HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH,
KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA,

MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI,
NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU,
RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM,
ZW.

(84) Designated States (*unless otherwise indicated, for every
kind of regional protection available*): ARIPO (BW, GH,
GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ,
UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ,
TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK,
EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV,
MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM,
TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW,
KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))

(54) Title: METHODS FOR ETCHING A SEMICONDUCTOR STRUCTURE AND FOR CONDITIONING A PROCESSING RE-
ACTOR

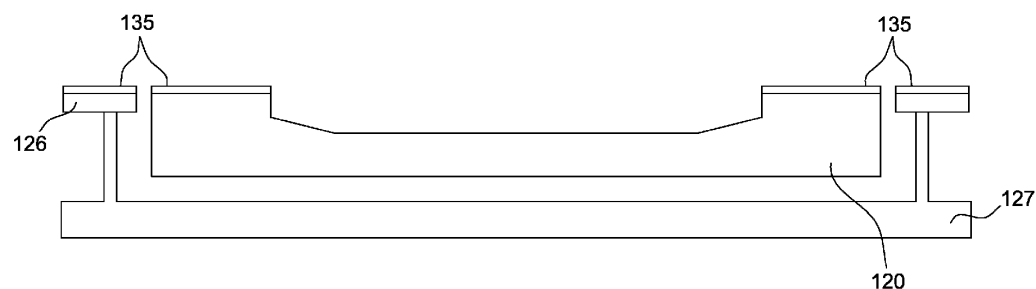


FIG. 4

(57) Abstract: Methods for etching a semiconductor structure and for conditioning a processing reactor in which a single semiconductor structure is treated are disclosed. An engineered polycrystalline silicon surface layer is deposited on a susceptor which supports the semiconductor structure. The polycrystalline silicon surface layer may be engineered by controlling the temperature at which the layer is deposited, by grooving the polycrystalline silicon surface layer or by controlling the thickness of the polycrystalline silicon surface layer.

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